Wafer Specifications

Material Properties	Crystal	Multicrystalline Silicon
	Oxygen concentration	≤8x10^{17} atoms/cm^{3}
	Carbon concentration	≤2x10^{18} atoms/cm^{3}
Electrical Properties	Specific resistivity	0.5-2.0 Ωcm
	Minority carrier lifetime (μ-PCD photoconductive decay)	≥1.8 μs
	Conduction type	P (Boron doped)
Geometrical Properties	Shape of wafer	Full Square
	Lengh of wafer edges	156.0 mm ±0.5 mm
	Bevel edge width	2±0.5 mm (hypotenuse)
	Bevel edge angle	45° ± 10°
	Average thickness	180 μm ± 20 μm, 200 μm ± 20 μm
	TTV	≤50 μm
Appearance	Corner chips	Length <5mm
	Cracks and pin holes	Depth <0.5 mm
		Max. Number per wafer: 3
		No cracks and pinholes visible with naked eye
	Surface	As cut and cleaned
	Saw Marks	No stains visible with naked eye
		Depth ≤20μm
	Crystal defects	No inclusions visible with naked eye
Process	Crystal growth technique	Direct Solidification
	Technique of Ingot formation	Casting by heat exchange method
	Squaring Technique	Wire sawing

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Solar Cells Hellas S.A. reserves the right to change the specifications at any time without prior notice.